

L	Hit	Search Text	DB	Time stamp
Number				
1		"DRAM or "dynamic random access memory"" : .PN.	USPAT; EPO; JPO; IBM_TDB	2003/01/16 13:54
2	43754	DRAM or "dynamic random access memory"	USPAT; EPO; JPO; IBM_TDB	2003/01/16 13:54
3	1905	cobalt or Co; same (HCl or hydrochloric or "hydrogen peroxide" or "H.sub.2O.sub.2")	USPAT; EPO; JPO; IBM_TDB	2003/01/16 15:33
4	9	DRAM or "dynamic random access memory" and cobalt or Co; same (HCl or hydrochloric or "hydrogen peroxide" or "H.sub.2O.sub.2")	USPAT; EPO; JPO; IBM_TDB	2003/01/16 14:00
11	87	cobalt or Co; same (HCl or hydrochloric or "hydrogen peroxide" or "H.sub.2O.sub.2") same (silicide or silicide) same (heat\$5 or anneal\$4 or sinter\$4)	USPAT; EPO; JPO; IBM_TDB	2003/01/16 15:12
12	138	cobalt or Co; and HCl or hydrochloric or "hydrogen peroxide" or "H.sub.2O.sub.2") and (silicide or silicide) and (heat\$5 or anneal\$4 or sinter\$4)	USPAT; EPO; JPO; IBM_TDB	2003/01/16 15:14
13	1101	cobalt or Co; and (HCl or hydrochloric or "hydrogen peroxide" or "H.sub.2O.sub.2") and (silicide or silicide) and (heat\$5 or anneal\$4 or sinter\$4) and etch\$4	USPAT; EPO; JPO; IBM_TDB	2003/01/16 15:14
14	68	cobalt or Co; and (HCl or hydrochloric or "hydrogen peroxide" or "H.sub.2O.sub.2") and (silicide or silicide) and (heat\$5 or anneal\$4 or sinter\$4) and etch\$4 and 438/\$.ccis. undr\$5 same (cobalt or Co; same (etch\$3 or remov\$3)	USPAT; EPO; JPO; IBM_TDB	2003/01/16 15:15
15			USPAT; EPO; JPO; IBM_TDB	2003/01/16 15:40
16	238	undr\$5 same (cobalt or Co; same etch\$3 or remov\$3)	USPAT; EPO; JPO; IBM_TDB	2003/01/16 15:40
17	9	undr\$5 same (cobalt or Co; same etch\$3 or remov\$3) and (DRAM or "dynamic random access memory")	USPAT; EPO; JPO; IBM_TDB	2003/01/16 15:41